



PNP BD684 – BD684A

SILICON DARLINGTON POWER TRANSISTORS

The BD684 and BD684A are PNP epitaxial-base transistors in monolithic Darlington circuit for audio and video applications.

They are mounted in Jedec TO-126 plastic package.

NPN complements are BD683 and BD683A.

Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{CBO}	Collector-Base Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	I_C	-4
		I_{CM}	-6
I_{BM}	Base current peak value	-0.1	A
P_T	Total power Dissipation @ $T_{mb} = 25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{Stg}	Storage Temperature	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-mb}	Thermal Resistance, Junction to mounting base	3.12	K/W
R_{thJ-a}	Thermal Resistance, Junction to ambient in free air	100	K/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit
I_{CBO}	Collector cut-off current	$I_E=0, V_{CB}=-120\text{ V}$	-	-	-0,2	mA
		$I_E=0, V_{CB}=-120\text{ V}, T_j=150^\circ\text{C}$	-	-	-2	
I_{CEO}	Collector cut-off current	$I_B=0, V_{CE}=-1/2V_{CEOMAX}$	-	-	-0,5	mA
I_{EBO}	Emitter cut-off current	$I_C=0, V_{EB}=-5\text{ V}$	-	-	-5	mA
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=-1.5\text{ A}$ $I_B=-30\text{ mA}$ BD683	-	-	-2,5	V
		$I_C=-2\text{ A}, I_B=-40\text{ mA}$ BD683A	-	-	-2,8	
h_{FE}	DC Current Gain (*)	$V_{CE}=-3\text{ V}, I_C=-1.5\text{ A}$ BD683	750	-	-	-
		$V_{CE}=-3\text{ V}, I_C=-2\text{ A}$ BD683A				
V_{BE}	Base-Emitter Voltage (*)	$V_{CE}=-3\text{ V}, I_C=-1.5\text{ A}$ BD683	-	-	-2,5	V
		$V_{CE}=-3\text{ V}, I_C=-2\text{ A}$ BD683A				
h_{fe}	Small signal current gain	$V_{CE}=-3\text{ V}, I_C=-1.5\text{ A}, f=1\text{ MHz}$	10	-	-	-
f_{hfe}	Ut-off frequency	$V_{CE}=-3\text{ V}, I_C=-1.5\text{ A}$	-	60	-	kHz
V_F	Diode forward voltage	$I_F=-1,5\text{ A}$	-	-1,5	-	V
$I_{(SB)}$	Second-breakdown collector current	$V_{CE}=-50\text{ V}, t_p=20\text{ms}$, non rep. without heatsink	-0,8	-	-	A
t_{on}	Turn-on time	$I_{con}=-1.5\text{ A}, I_{bon}=-I_{boff}=-6\text{mA}$	-	0,8	2	μs
t_{off}	Turn-off time	$V_{CC}=-30\text{V}$	-	4,5	8	

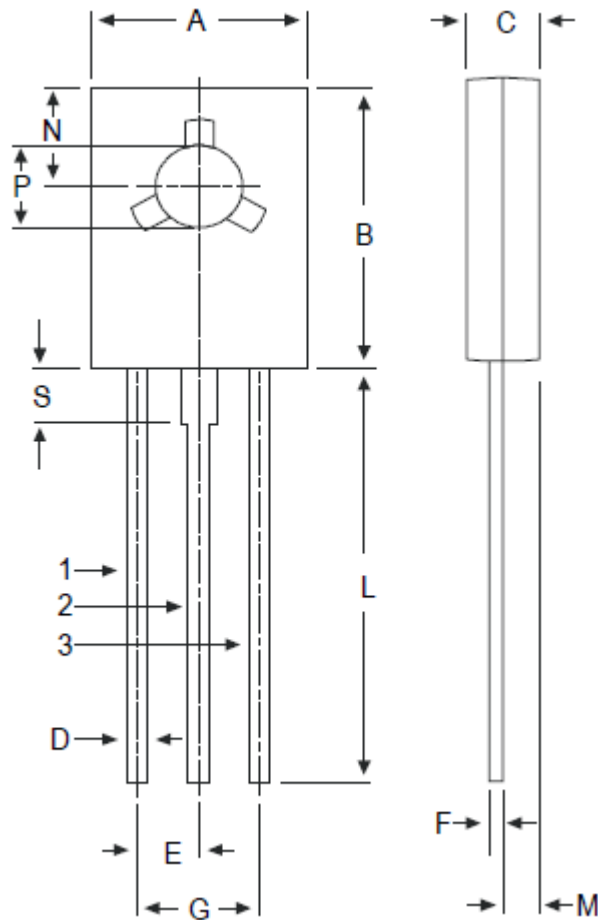
(*) Measured under pulse conditions : $t_p < 300\mu\text{s}$, $\delta < 2\%$.

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MECHANICAL DATA CASE TO-126

	DIMENSIONS	
	min	max
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 typ.	
F	0.49	0.75
G	4.4 typ.	
L	15.7 typ.	
M	1.27 typ.	
N	3.75 typ.	
P	3.0	3.2
S	2.54 typ.	

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



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